

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,087,529 B2
APPLICATION NO. : 10/677433
DATED : August 8, 2006
INVENTOR(S) : Fang et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, Item (57) Abstract, After,

“A chemical-mechanical abrasive composition for use in semiconductor processing uses abrasive particles having a non-spherical morphology.” insert -- Compositions and methods for planarizing or polishing a surface, particularly a semiconductor wafer surface. The polishing compositions described herein comprise (a) a liquid carrier; (b) purified clay; and optional additives, such as (c) a chemical accelerator; and (d) a complexing or coupling agent capable of chemically or ionically complexing with, or coupling to, the metal and/or insulating material removed during the polishing process. The complexing or coupling agent carries away the removed metal and/or silicon dioxide insulator particles, during polishing, to prevent the separated particles from returning to the surface from which they were removed. Also disclosed are methods of planarizing or polishing a surface comprising contacting the surface with the compositions. --

Signed and Sealed this

Sixth Day of March, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office